

# NTD14N03R, NVD14N03R

## Power MOSFET

14 A, 25 V, N-Channel DPAK

### Features

- Planar HD3e Process for Fast Switching Performance
- Low  $R_{DS(on)}$  to Minimize Conduction Loss
- Low  $C_{iss}$  to Minimize Driver Loss
- Low Gate Charge
- Optimized for High Side Switching Requirements in High-Efficiency DC-DC Converters
- NVD and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter                                                                      | Symbol          | Value          | Unit               |
|--------------------------------------------------------------------------------|-----------------|----------------|--------------------|
| Drain-to-Source Voltage                                                        | $V_{DS}$        | 25             | Vdc                |
| Gate-to-Source Voltage – Continuous                                            | $V_{GS}$        | $\pm 20$       | Vdc                |
| Thermal Resistance – Junction-to-Case                                          | $R_{\theta JC}$ | 6.0            | $^\circ\text{C/W}$ |
| Total Power Dissipation @ $T_A = 25^\circ\text{C}$                             | $P_D$           | 20.8           | W                  |
| Drain Current – Continuous @ $T_A = 25^\circ\text{C}$ , Chip                   | $I_D$           | 14             | A                  |
| – Continuous @ $T_A = 25^\circ\text{C}$ , Limited by Package                   | $I_D$           | 11.4           | A                  |
| – Single Pulse ( $t_p \leq 10 \mu\text{s}$ )                                   | $I_D$           | 28             | A                  |
| Thermal Resistance, Junction-to-Ambient (Note 1)                               | $R_{\theta JA}$ | 80             | $^\circ\text{C/W}$ |
| Total Power Dissipation @ $T_A = 25^\circ\text{C}$                             | $P_D$           | 1.56           | W                  |
| Drain Current – Continuous @ $T_A = 25^\circ\text{C}$                          | $I_D$           | 3.1            | A                  |
| Thermal Resistance, Junction-to-Ambient (Note 2)                               | $R_{\theta JA}$ | 120            | $^\circ\text{C/W}$ |
| Total Power Dissipation @ $T_A = 25^\circ\text{C}$                             | $P_D$           | 1.04           | W                  |
| Drain Current – Continuous @ $T_A = 25^\circ\text{C}$                          | $I_D$           | 2.5            | A                  |
| Operating and Storage Temperature Range                                        | $T_J, T_{stg}$  | $-55$ to $150$ | $^\circ\text{C}$   |
| Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds | $T_L$           | 260            | $^\circ\text{C}$   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. When surface mounted to an FR4 board using 0.5 sq. in pad size.
2. When surface mounted to an FR4 board using minimum recommended pad size.

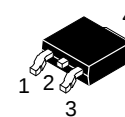
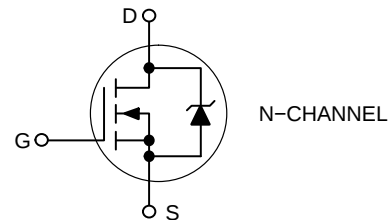


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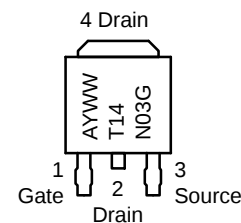
14 AMPERES, 25 VOLTS

$R_{DS(on)} = 70.4 \text{ m}\Omega$  (Typ)



DPAK  
CASE 369C  
(Surface Mount)  
STYLE 2

### MARKING DIAGRAM & PIN ASSIGNMENTS



A = Assembly Location\*  
Y = Year  
WW = Work Week  
14N03 = Device Code  
G = Pb-Free Package

\* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# NTD14N03R, NVD14N03R

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

| Characteristics | Symbol | Min | Typ | Max | Unit |
|-----------------|--------|-----|-----|-----|------|
|-----------------|--------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                                                                                                                                       |                      |         |         |           |              |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------|---------|---------|-----------|--------------|
| Drain-to-Source Breakdown Voltage (Note 3)<br>(V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 250 μAdc)<br>Temperature Coefficient (Positive)                              | V <sub>(br)DSS</sub> | 25<br>– | 28<br>– | –<br>–    | Vdc<br>mV/°C |
| Zero Gate Voltage Drain Current<br>(V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc)<br>(V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 150°C) | I <sub>DSS</sub>     | –<br>–  | –<br>–  | 1.0<br>10 | μAdc         |
| Gate-Body Leakage Current<br>(V <sub>GS</sub> = ±20 Vdc, V <sub>DS</sub> = 0 Vdc)                                                                                     | I <sub>GSS</sub>     | –       | –       | ±100      | nAdc         |

### ON CHARACTERISTICS (Note 3)

|                                                                                                                                                            |                     |          |             |           |              |
|------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------|----------|-------------|-----------|--------------|
| Gate Threshold Voltage (Note 3)<br>(V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μAdc)<br>Threshold Temperature Coefficient (Negative)         | V <sub>GS(th)</sub> | 1.0<br>– | 1.5<br>–    | 2.0<br>–  | Vdc<br>mV/°C |
| Static Drain-to-Source On-Resistance (Note 3)<br>(V <sub>GS</sub> = 4.5 Vdc, I <sub>D</sub> = 5 Adc)<br>(V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 5 Adc) | R <sub>DS(on)</sub> | –<br>–   | 117<br>70.4 | 130<br>95 | mΩ           |
| Forward Transconductance (Note 3)<br>(V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 5 Adc)                                                                    | g <sub>FS</sub>     | –        | 7.0         | –         | Mhos         |

### DYNAMIC CHARACTERISTICS

|                      |                                                              |                  |   |     |   |    |
|----------------------|--------------------------------------------------------------|------------------|---|-----|---|----|
| Input Capacitance    | (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 V, f = 1 MHz) | C <sub>iss</sub> | – | 115 | – | pF |
| Output Capacitance   |                                                              | C <sub>oss</sub> | – | 62  | – |    |
| Transfer Capacitance |                                                              | C <sub>rss</sub> | – | 33  | – |    |

### SWITCHING CHARACTERISTICS (Note 4)

|                     |                                                                                                       |                     |   |     |   |    |
|---------------------|-------------------------------------------------------------------------------------------------------|---------------------|---|-----|---|----|
| Turn-On Delay Time  | (V <sub>GS</sub> = 10 Vdc, V <sub>DD</sub> = 10 Vdc,<br>I <sub>D</sub> = 5 Adc, R <sub>G</sub> = 3 Ω) | t <sub>d(on)</sub>  | – | 3.8 | – | ns |
| Rise Time           |                                                                                                       | t <sub>r</sub>      | – | 27  | – |    |
| Turn-Off Delay Time |                                                                                                       | t <sub>d(off)</sub> | – | 9.6 | – |    |
| Fall Time           |                                                                                                       | t <sub>f</sub>      | – | 2.0 | – |    |
| Gate Charge         | (V <sub>GS</sub> = 5 Vdc, I <sub>D</sub> = 5 Adc,<br>V <sub>DS</sub> = 10 Vdc) (Note 3)               | Q <sub>T</sub>      | – | 1.8 | – | nC |
|                     |                                                                                                       | Q <sub>1</sub>      | – | 0.8 | – |    |
|                     |                                                                                                       | Q <sub>2</sub>      | – | 0.7 | – |    |

### SOURCE-DRAIN DIODE CHARACTERISTICS

|                                |                                                                                                                                         |                 |        |              |          |     |
|--------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------|-----------------|--------|--------------|----------|-----|
| Forward On-Voltage             | (I <sub>S</sub> = 5 Adc, V <sub>GS</sub> = 0 Vdc) (Note 3)<br>(I <sub>S</sub> = 5 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C) | V <sub>SD</sub> | –<br>– | 0.93<br>0.82 | 1.2<br>– | Vdc |
| Reverse Recovery Time          | (I <sub>S</sub> = 5 Adc, V <sub>GS</sub> = 0 Vdc,<br>di <sub>S</sub> /dt = 100 A/μs) (Note 3)                                           | t <sub>rr</sub> | –      | 6.6          | –        | ns  |
|                                |                                                                                                                                         | t <sub>a</sub>  | –      | 4.75         | –        |     |
|                                |                                                                                                                                         | t <sub>b</sub>  | –      | 1.88         | –        |     |
| Reverse Recovery Stored Charge |                                                                                                                                         | Q <sub>RR</sub> | –      | 0.002        | –        | μC  |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

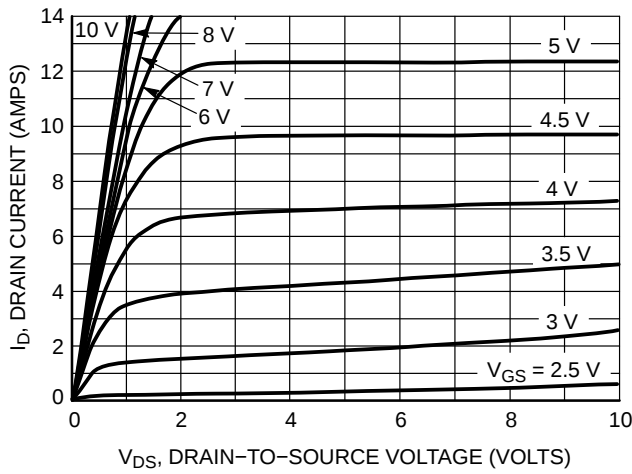


Figure 1. On-Region Characteristics

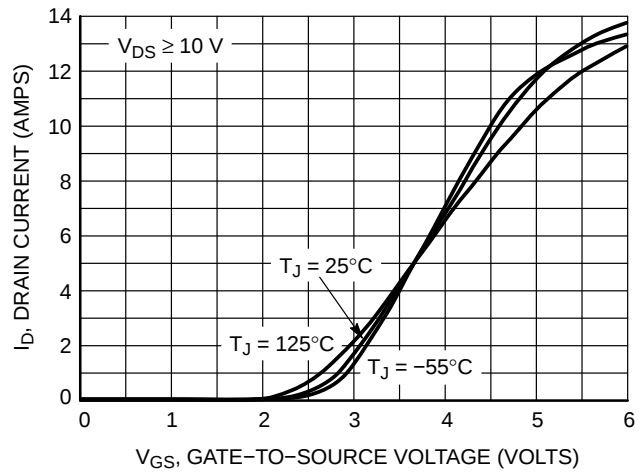


Figure 2. Transfer Characteristics

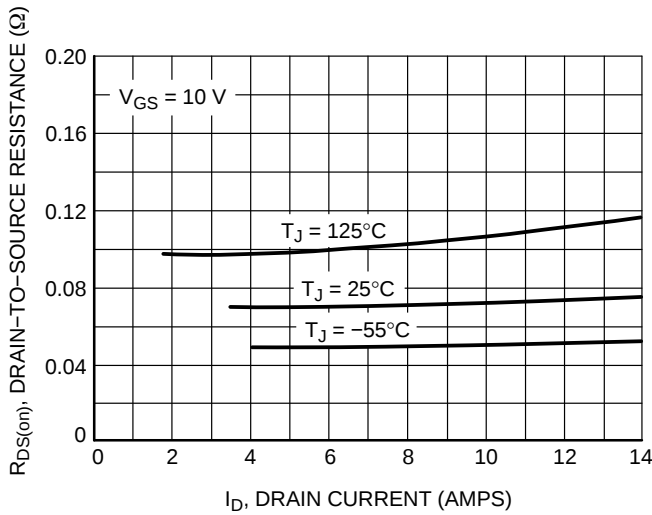


Figure 3. On-Resistance versus Drain Current and Temperature

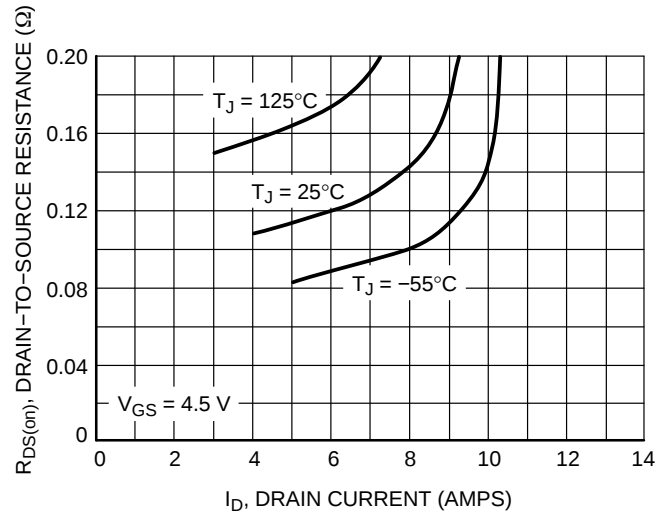


Figure 4. On-Resistance versus Drain Current and Temperature

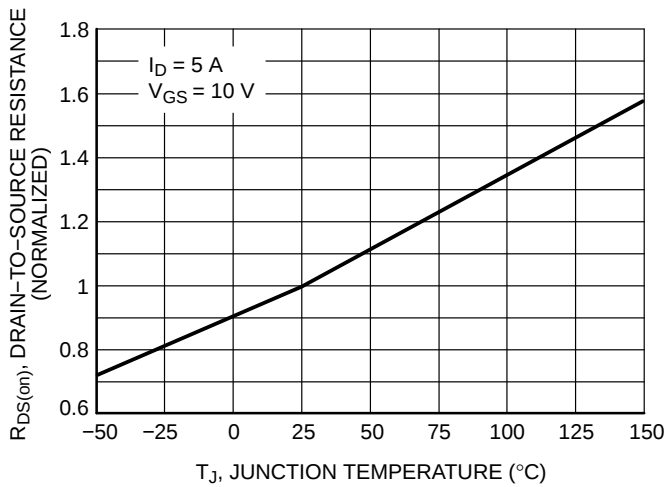


Figure 5. On-Resistance Variation with Temperature

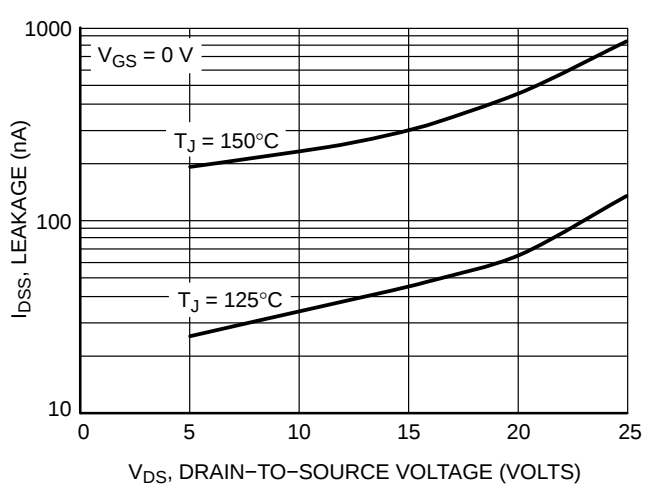


Figure 6. Drain-to-Source Leakage Current versus Voltage

# NTD14N03R, NVD14N03R

## TYPICAL CHARACTERISTICS

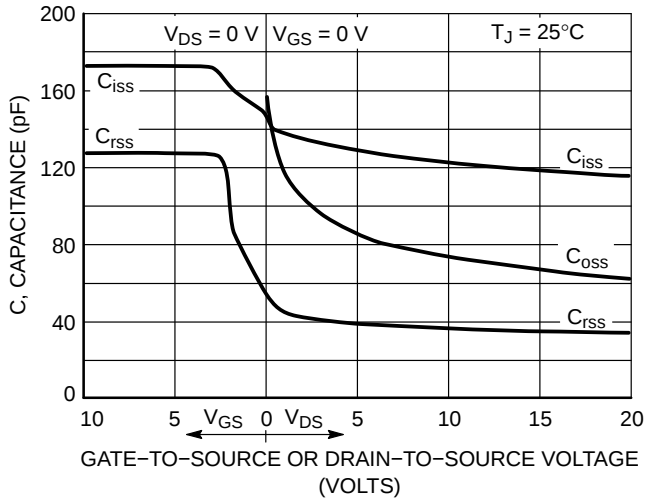


Figure 7. Capacitance Variation

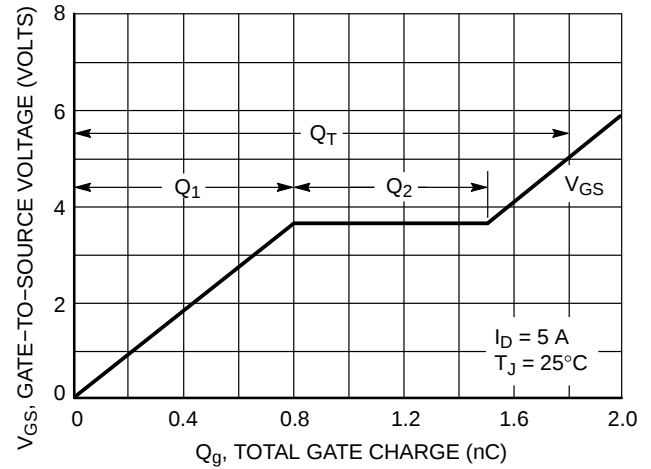


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

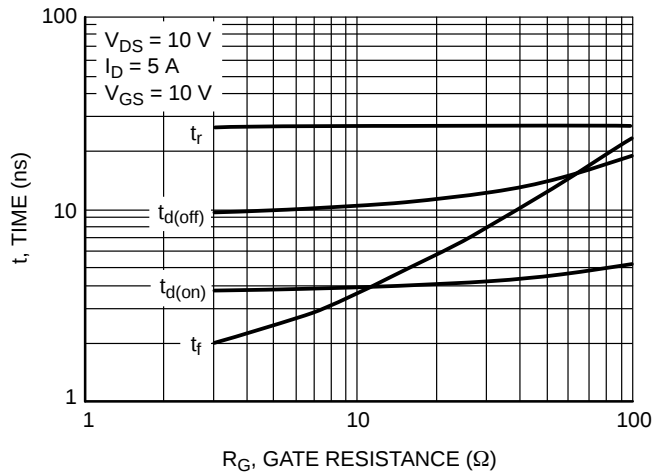


Figure 9. Resistive Switching Time Variation versus Gate Resistance

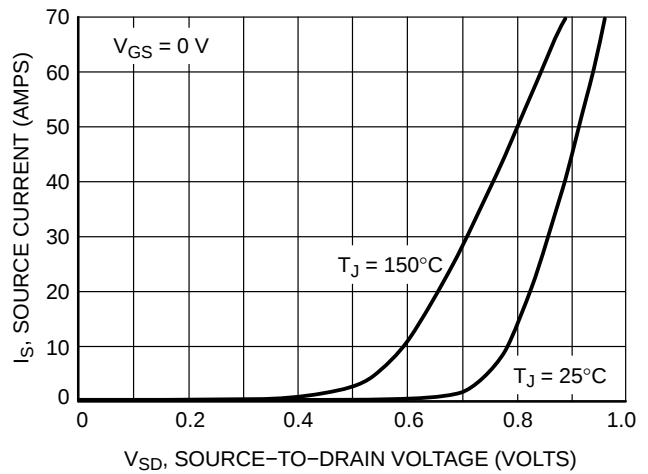


Figure 10. Diode Forward Voltage versus Current

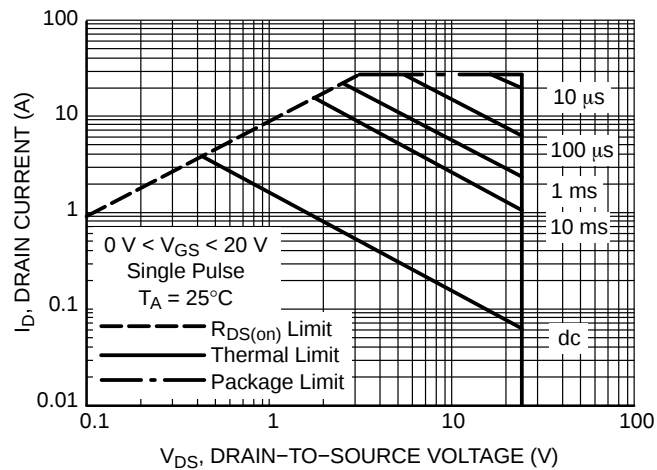


Figure 11. Maximum Rated Forward Biased Safe Operating Area

# NTD14N03R, NVD14N03R

## TYPICAL CHARACTERISTICS

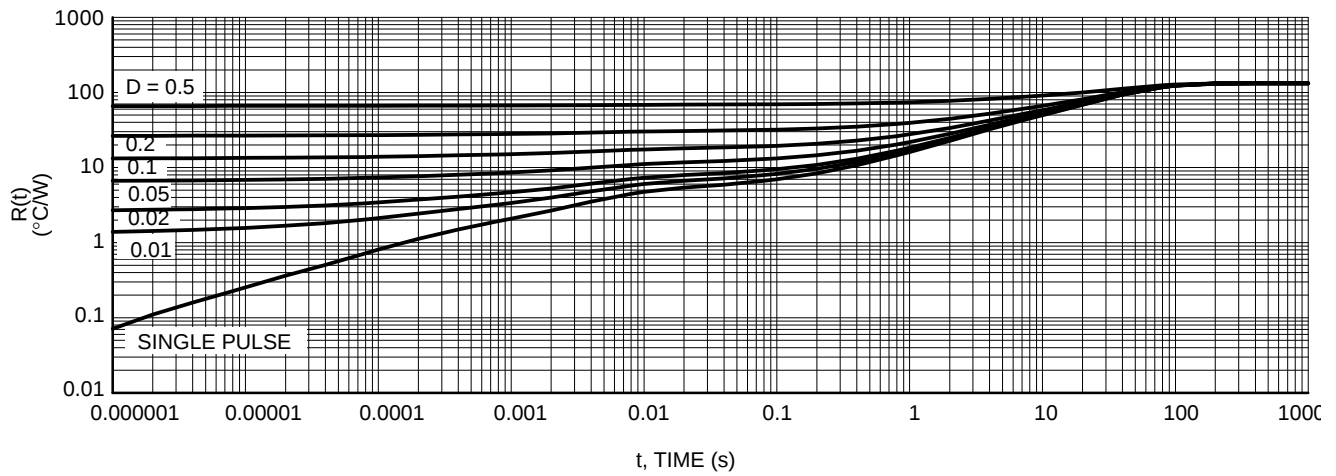


Figure 12. Thermal Response

### ORDERING INFORMATION

| Device        | Package           | Shipping <sup>†</sup> |
|---------------|-------------------|-----------------------|
| NTD14N03RT4G  | DPAK<br>(Pb-Free) | 2500 / Tape & Reel    |
| NVD14N03RT4G* | DPAK<br>(Pb-Free) | 2500 / Tape & Reel    |
| SVD14N03RT4G* | DPAK<br>(Pb-Free) | 2500 / Tape & Reel    |

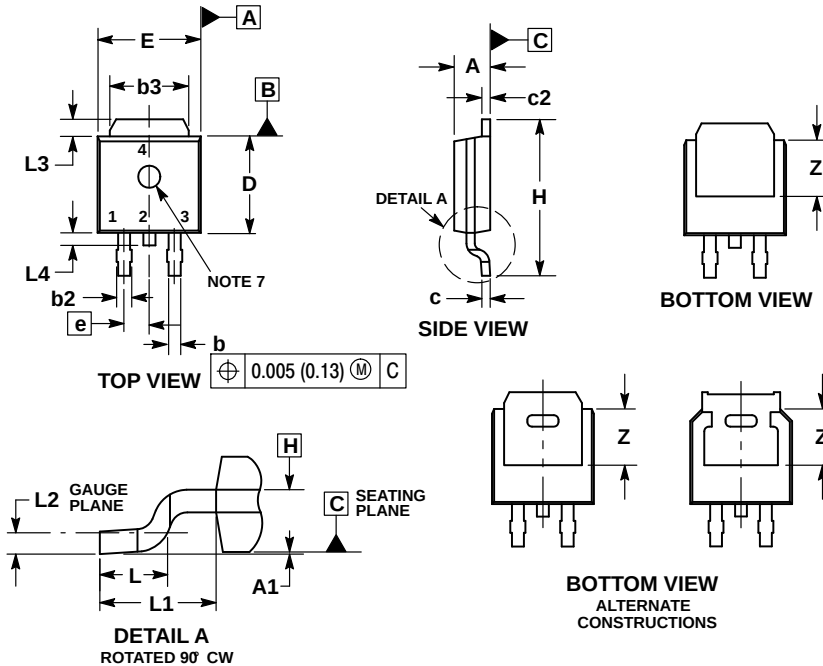
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NVD and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

# NTD14N03R, NVD14N03R

## PACKAGE DIMENSIONS

### DPAK (SINGLE GAUGE) CASE 369C ISSUE F



#### NOTES:

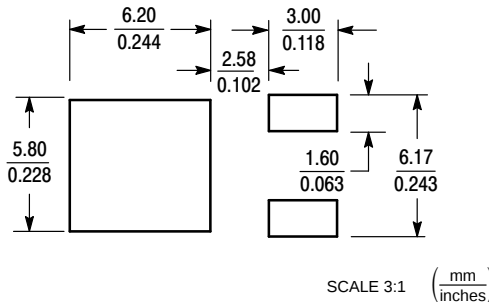
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 0.086  | 0.094 | 2.18        | 2.38  |
| A1  | 0.000  | 0.005 | 0.00        | 0.13  |
| b   | 0.025  | 0.035 | 0.63        | 0.89  |
| b2  | 0.028  | 0.045 | 0.72        | 1.14  |
| b3  | 0.180  | 0.215 | 4.57        | 5.46  |
| c   | 0.018  | 0.024 | 0.46        | 0.61  |
| c2  | 0.018  | 0.024 | 0.46        | 0.61  |
| D   | 0.235  | 0.245 | 5.97        | 6.22  |
| E   | 0.250  | 0.265 | 6.35        | 6.73  |
| e   | 0.090  | BSC   | 2.29        | BSC   |
| H   | 0.370  | 0.410 | 9.40        | 10.41 |
| L   | 0.055  | 0.070 | 1.40        | 1.78  |
| L1  | 0.114  | REF   | 2.90        | REF   |
| L2  | 0.020  | BSC   | 0.51        | BSC   |
| L3  | 0.035  | 0.050 | 0.89        | 1.27  |
| L4  | ---    | 0.040 | ---         | 1.01  |
| Z   | 0.155  | ---   | 3.93        | ---   |

#### STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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